Docket No.: 51876P453

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

SOON-YONG KWEON, ET AL.

Art Group:

Application No.:

Examiner:

Filed:

For: METHOD FOR FABRICATING

FERROELECTRIC RANDOM ACCESS

MEMORY DEVICE

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s). Copies of the references cited on PTO/SB/08 are enclosed herewith.

-1- 51876P453

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

Blakely, Sokołoff, Waylor & Zafman LLI

Eric S. Hyman, Reg. No. 30,139

12400 Wilshire Boulevard, 7th Floor

Date: December 17, 2003

Los Angeles, CA 90025 Telephone: (310) 207-3800

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	U.S. PATENT DOCUMENTS						
Document Number  Publication Date  Name of Patentee or  Pages.							
Examiner Initials*	Cite No.1		Publication Date or Issue Date MM-DD-YYYY	Name of Patenties or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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	FOREIGN PATENT DOCUMENTS							
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	No.¹	Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		KR 2003-23844	03-20-2003	Hynix Semiconductor Inc.				
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Signature		Considered	1	

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<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date		
				First Named Inventor	Soon-Yong Kweon	
				Art Unit		
				Examiner Name		
Sheet	2	of	2	Attorney Docket Number	51876P453	

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
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